Tokyo Electron Ltd. Trias Ti/TiN
Metal CVD (Chemical Vapor Deposition)

Currently Configured for 300mm wafer size
MFG Date: March 27, 2002

EQUIPMENT DETAILS:
Tool is operating in clean room.
Labelled as Collateral Asset.

[Chamber A]
Process: TiN
Hard: SFD
Gas(sccm): $TiCl_4$(100), ClF_3(500), N_2(600/2000), NH_3(5000), NH_3(300), N_2(600/2000), NH_3(1000), N_2(300)

[Chamber B]
Process: TiN
Hard: SFD
Gas(sccm): $TiCl_4$(100), ClF_3(500), N_2(600/2000), NH_3(5000), NH_3(300), N_2(600/2000), NH_3(1000), N_2(300)

[Chamber C]
Process: TiN
Hard: SFD
Gas(sccm): $TiCl_4$(100), ClF_3(500), N_2(600/2000), NH_3(5000), NH_3(300), N_2(600/2000), NH_3(1000), N_2(300)